

CoolSiC™ 1200 V SiC Trench MOSFET : silicon carbide MOSFET

Features

- $V_{DSS} = 1200\text{ V}$ at $T_{vj} = 25^\circ\text{C}$
- $I_{DCC} = 225\text{ A}$ at $T_{vj} = 25^\circ\text{C}$
- $R_{DS(on)} = 7\text{ m}\Omega$ at $V_{GS} = 18\text{ V}$, $T_{vj} = 25^\circ\text{C}$
- Very low switching losses
- Benchmark gate threshold voltage, $V_{GS(th)} = 4.2\text{ V}$
- Robust against parasitic turn on, 0 V turn-off gate voltage can be applied
- Robust body diode for hard commutation
- .XT interconnection technology for best-in-class thermal performance

Potential applications

- General purpose drives (GPD)
- EV-Charging
- Online UPS/Industrial UP
- String inverters
- Solar optimizer

Product validation

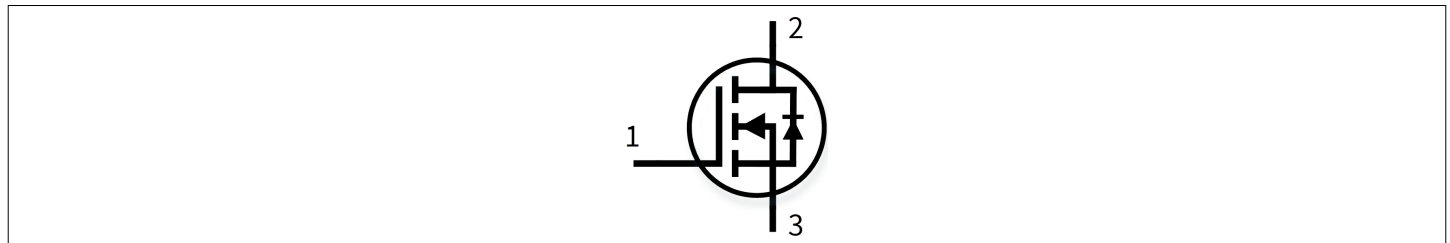
- Qualified for industrial applications according to the relevant tests of JEDEC47/20/22
- Please also note the application note AN2019-05 for power and thermal cycling



- Lead-Free
- Green
- Halogen-Free
- RoHS

Description

- 1 – gate
- 2 – drain
- 3 – source



Type	Package	Marking
IMW120R007M1H	PG-TO247-3-STD-N2.5	12M1H007

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1 Package

Table 1 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature		wave soldering 1.6 mm (0.063 in.) from case for 10 s			260	°C
Mounting torque	M	M3 screw Maximum of mounting process: 3			0.6	Nm
Thermal resistance, junction-ambient	$R_{th(j-a)}$				62	K/W

2 MOSFET

Table 2 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Drain-source voltage	V_{DSS}	$T_{vj} \geq 25\text{ °C}$	1200	V	
Continuous DC drain current for $R_{th(j-c,max)}$, limited by $T_{vj(max)}$	I_{DDC}	$V_{GS} = 18\text{ V}$	$T_c = 25\text{ °C}$	225	A
			$T_c = 100\text{ °C}$	168	
Peak drain current, t_p limited by $T_{vj(max)}$	I_{DM}	$V_{GS} = 18\text{ V}$	504	A	
Gate-source voltage, max. transient voltage ¹⁾	V_{GS}	$t_p \leq 0.5\ \mu\text{s}$, $D < 0.001$	-10/23	V	
Gate-source voltage, max. static voltage	V_{GS}		-5/20	V	
Avalanche energy, single pulse	E_{AS}	$I_D = 35\text{ A}$, $V_{DD} = 50\text{ V}$, $L = 1\text{ mH}$	638	mJ	
Avalanche energy, repetitive	E_{AR}	$I_D = 35\text{ A}$, $V_{DD} = 50\text{ V}$, $L = 5.2\ \mu\text{H}$	3.2	mJ	
MOSFET dv/dt robustness	dv/dt	$V_{DS} = 0 \dots 800\text{ V}$	150	V/ns	
Power dissipation, limited by $T_{vj(max)}$	P_{tot}		$T_c = 25\text{ °C}$	750	W
			$T_c = 100\text{ °C}$	375	

¹⁾ Important note: The selection of positive and negative gate-source voltages impacts the long-term behavior of the device. The design guidelines described in Application Note AN2018-09 must be considered to ensure sound operation of the device over the planned lifetime.

Table 3 Recommended values

Parameter	Symbol	Note or test condition	Values	Unit
Recommended turn-on gate voltage	$V_{GS(on)}$		15...18	V

(table continues...)

Table 3 (continued) Recommended values

Parameter	Symbol	Note or test condition	Values	Unit
Recommended turn-off gate voltage	$V_{GS(off)}$		-5...0	V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Drain-source on-state resistance	$R_{DS(on)}$	$I_D = 108\text{ A}$	$T_{vj} = 25\text{ °C}$, $V_{GS(on)} = 18\text{ V}$		7	9.9	mΩ
			$T_{vj} = 100\text{ °C}$, $V_{GS(on)} = 18\text{ V}$		10		
			$T_{vj} = 175\text{ °C}$, $V_{GS(on)} = 18\text{ V}$		14		
			$T_{vj} = 25\text{ °C}$, $V_{GS(on)} = 15\text{ V}$		8.9	11.1	
Gate-emitter threshold voltage	$V_{GS(th)}$	$I_D = 47\text{ mA}$, $V_{DS} = V_{GS}$ (tested after 1 ms pulse at $V_{GS} = 20\text{ V}$)	$T_{vj} = 25\text{ °C}$	3.5	4.2	5.2	V
			$T_{vj} = 175\text{ °C}$		3.6		
Zero gate-voltage drain current	I_{DSS}	$V_{DS} = 1200\text{ V}$, $V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$			860	μA
			$T_{vj} = 175\text{ °C}$		15		
Gate leakage current	I_{GSS}	$V_{DS} = 0\text{ V}$	$V_{GS} = 23\text{ V}$			300	nA
			$V_{GS} = -10\text{ V}$			-300	
Forward transconductance	g_{fs}	$I_D = 108\text{ A}$, $V_{DS} = 20\text{ V}$		72.6		S	
Internal gate resistance	$R_{G,int}$	$f = 1\text{ MHz}$, $V_{AC} = 25\text{ mV}$		1.8		Ω	
Input capacitance	C_{iss}	$V_{DD} = 25\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 100\text{ kHz}$, $V_{AC} = 25\text{ mV}$		9170		nF	
Output capacitance	C_{oss}	$V_{DD} = 25\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 100\text{ kHz}$, $V_{AC} = 25\text{ mV}$		420		pF	
Reverse transfer capacitance	C_{rss}	$V_{DD} = 25\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 100\text{ kHz}$, $V_{AC} = 25\text{ mV}$		61		pF	
C_{oss} stored energy	E_{oss}	$V_{DD} = 25\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 100\text{ kHz}$, $V_{AC} = 25\text{ mV}$		172		μJ	
Total gate charge	Q_G	$V_{DD} = 800\text{ V}$, $I_D = 108\text{ A}$, $V_{GS} = 0/18\text{ V}$, turn-on pulse		220		nC	
Plateau gate charge	$Q_{GS(pl)}$	$V_{DD} = 800\text{ V}$, $I_D = 108\text{ A}$, $V_{GS} = 0/18\text{ V}$, turn-on pulse		72		nC	
Gate-to-drain charge	Q_{GD}	$V_{DD} = 800\text{ V}$, $I_D = 108\text{ A}$, $V_{GS} = 0/18\text{ V}$, turn-on pulse		64		nC	

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 800\text{ V}, I_D = 108\text{ A},$ $V_{GS} = 0/18\text{ V},$ $R_{GS(on)} = 1\ \Omega,$ $R_{GS(off)} = 1\ \Omega,$ diode: body diode at $V_{GS} = 0\text{ V},$ $L_\sigma = 15\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$		62	ns
			$T_{vj} = 175\text{ }^\circ\text{C}$		55	
Rise time	t_r	$V_{DD} = 800\text{ V}, I_D = 108\text{ A},$ $V_{GS} = 0/18\text{ V},$ $R_{GS(on)} = 1\ \Omega,$ $R_{GS(off)} = 1\ \Omega,$ diode: body diode at $V_{GS} = 0\text{ V},$ $L_\sigma = 15\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$		58	ns
			$T_{vj} = 175\text{ }^\circ\text{C}$		75	
Turn-off delay time	$t_{d(off)}$	$V_{DD} = 800\text{ V}, I_D = 108\text{ A},$ $V_{GS} = 0/18\text{ V},$ $R_{GS(on)} = 1\ \Omega,$ $R_{GS(off)} = 1\ \Omega,$ diode: body diode at $V_{GS} = 0\text{ V},$ $L_\sigma = 15\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$		77	ns
			$T_{vj} = 175\text{ }^\circ\text{C}$		85	
Fall time	t_f	$V_{DD} = 800\text{ V}, I_D = 108\text{ A},$ $V_{GS} = 0/18\text{ V},$ $R_{GS(on)} = 1\ \Omega,$ $R_{GS(off)} = 1\ \Omega,$ diode: body diode at $V_{GS} = 0\text{ V},$ $L_\sigma = 15\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$		44	ns
			$T_{vj} = 175\text{ }^\circ\text{C}$		44	
Turn-on energy	E_{on}	$V_{DD} = 800\text{ V}, I_D = 108\text{ A},$ $V_{GS} = 0/18\text{ V},$ $R_{GS(on)} = 1\ \Omega,$ $R_{GS(off)} = 1\ \Omega,$ diode: body diode at $V_{GS} = 0\text{ V},$ $L_\sigma = 15\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$		2900	μJ
			$T_{vj} = 175\text{ }^\circ\text{C}$		3470	
Turn-off energy	E_{off}	$V_{DD} = 800\text{ V}, I_D = 108\text{ A},$ $V_{GS} = 0/18\text{ V},$ $R_{GS(on)} = 1\ \Omega,$ $R_{GS(off)} = 1\ \Omega,$ diode: body diode at $V_{GS} = 0\text{ V},$ $L_\sigma = 15\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$		1200	μJ
			$T_{vj} = 175\text{ }^\circ\text{C}$		1320	
Total switching energy	E_{tot}	$V_{DD} = 800\text{ V}, I_D = 108\text{ A},$ $V_{GS} = 0/18\text{ V},$ $R_{GS(on)} = 1\ \Omega,$ $R_{GS(off)} = 1\ \Omega,$ diode: body diode at $V_{GS} = 0\text{ V},$ $L_\sigma = 15\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$		4561	μJ
			$T_{vj} = 175\text{ }^\circ\text{C}$		6028	

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
MOSFET/body diode thermal resistance, junction to case	$R_{th(j-c)}$			0.15	0.20	K/W
Virtual junction temperature	T_{vj}		-55		175	°C

Note: For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

The chip technology was characterized up to 200 kV/μs. The measured dV/dt was limited by measurement test setup and package.

Dynamic test circuit see Fig. F.

3 Body diode

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Drain-source voltage	V_{DSS}	$T_{vj} \geq 25\text{ °C}$	1200	V	
Continuous reverse drain current for $R_{th(j-c,max)}$, limited by $T_{vj(max)}$	I_{SDC}	$V_{GS} = 0\text{ V}$	$T_c = 25\text{ °C}$	163	A
			$T_c = 100\text{ °C}$	93	
Peak reverse drain current, t_p limited by $T_{vj(max)}$	I_{SM}	$V_{GS} = 0\text{ V}$	504	A	

Table 6 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Drain-source reverse voltage	V_{SD}	$I_{SD} = 108\text{ A}, V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$	3.8	5	V
			$T_{vj} = 100\text{ °C}$	3.7		
			$T_{vj} = 175\text{ °C}$	3.6		
MOSFET forward recovery charge	Q_{fr}	$V_{DD} = 800\text{ V}, I_{SD} = 108\text{ A}, V_{GS} = 0\text{ V}, di_i/dt = 3000\text{ A}/\mu\text{s}, Q_{fr}$ includes also Q_C	$T_{vj} = 25\text{ °C}$	900		nC
			$T_{vj} = 175\text{ °C}$	1651		
MOSFET peak forward recovery current	I_{frm}	$V_{DD} = 800\text{ V}, I_{SD} = 108\text{ A}, V_{GS} = 0\text{ V}, di_i/dt = 3000\text{ A}/\mu\text{s}, Q_{fr}$ includes also Q_C	$T_{vj} = 25\text{ °C}$	7		A
			$T_{vj} = 175\text{ °C}$	8		

(table continues...)

Table 6 (continued) **Characteristic values**

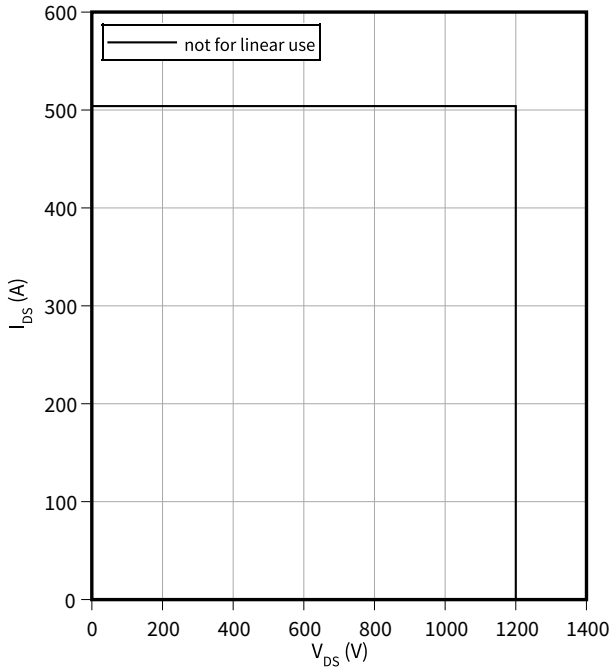
Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
MOSFET forward recovery energy	E_{fr}	$V_{DD} = 800 \text{ V}$, $I_{SD} = 108 \text{ A}$, $V_{GS} = 0 \text{ V}$, $di_f/dt = 3000 \text{ A}/\mu\text{s}$, Q_{fr} includes also Q_C	$T_{vj} = 25 \text{ }^\circ\text{C}$		461	μJ
			$T_{vj} = 175 \text{ }^\circ\text{C}$		1238	
Virtual junction temperature	T_{vj}		-55		175	$^\circ\text{C}$

4 Characteristics diagrams

Reverse bias safe operating area (RBSOA), MOSFET

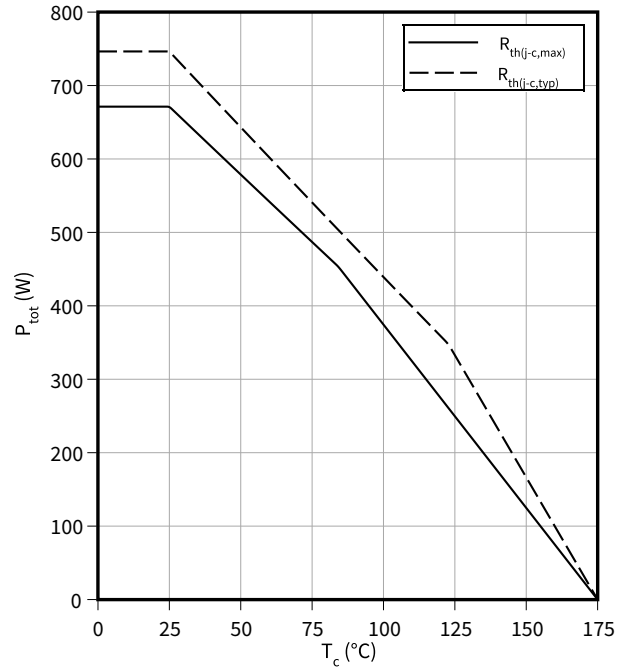
$$I_{DS} = f(V_{DS})$$

$$T_{vj} \leq 175\text{ °C}, V_{GS} = 0/18\text{ V}, T_c = 25\text{ °C}$$



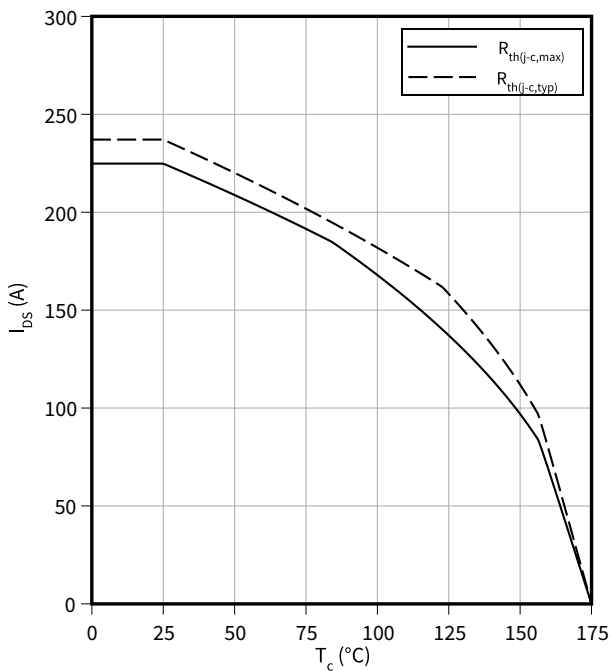
Power dissipation as a function of case temperature limited by bond wire, MOSFET

$$P_{tot} = f(T_c)$$



Maximum DC drain to source current as a function of case temperature limited by bond wire, MOSFET

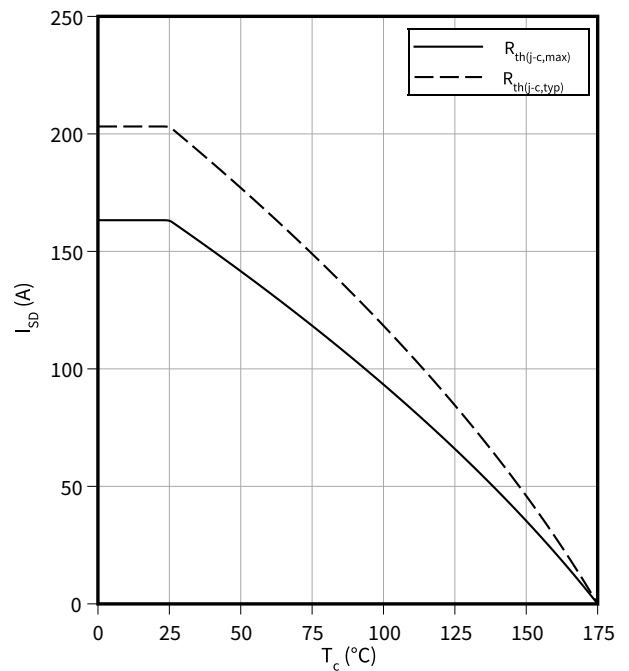
$$I_{DS} = f(T_c)$$



Maximum source to drain current as a function of case temperature limited by bond wire, MOSFET

$$I_{SD} = f(T_c)$$

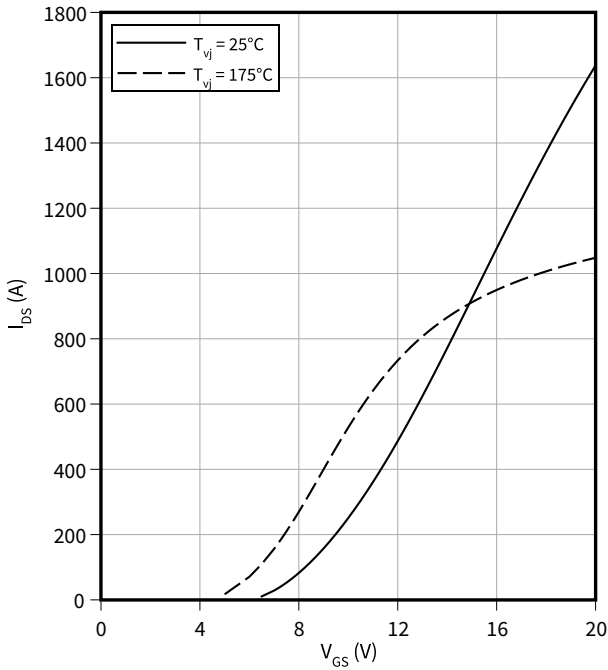
$$V_{GS} = 0\text{ V}$$



4 Characteristics diagrams

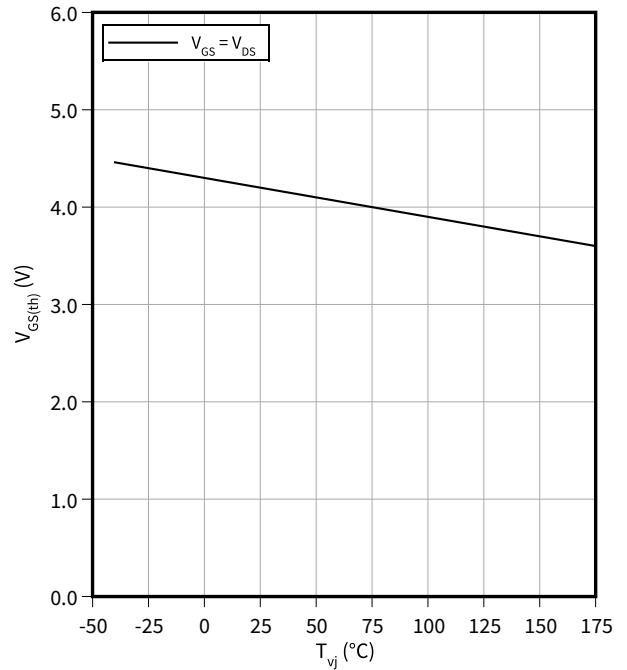
Typical transfer characteristic, MOSFET

$I_{DS} = f(V_{GS})$
 $V_{DS} = 20\text{ V}$, $t_p = 20\ \mu\text{s}$



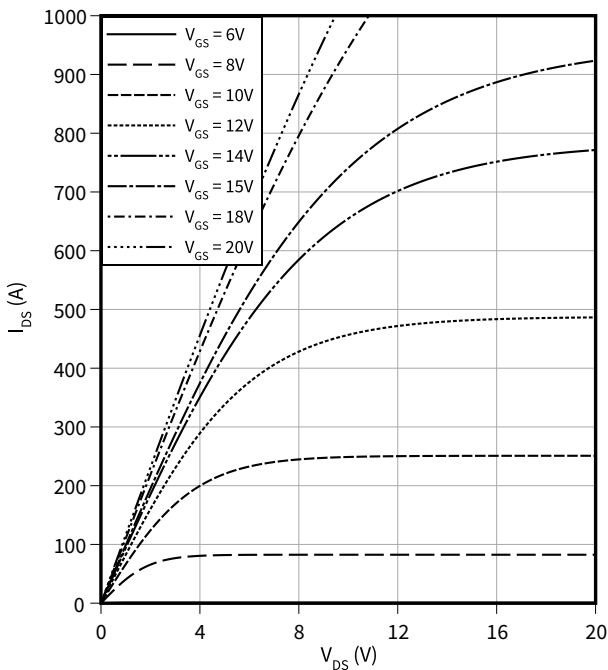
Typical gate-source threshold voltage as a function of junction temperature, MOSFET

$V_{GS(th)} = f(T_{vj})$
 $I_D = 47\text{ mA}$



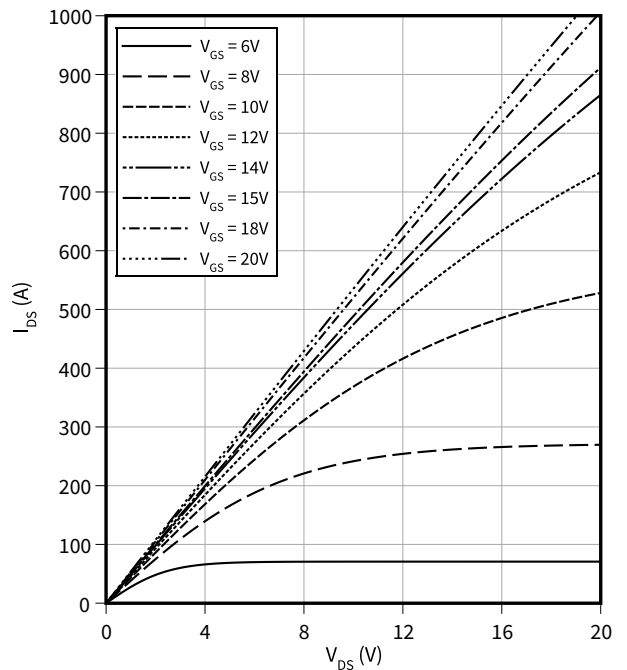
Typical output characteristic, V_{GS} as parameter, MOSFET

$I_{DS} = f(V_{DS})$
 $T_{vj} = 25\text{ °C}$, $t_p = 20\ \mu\text{s}$



Typical output characteristic, V_{GS} as parameter, MOSFET

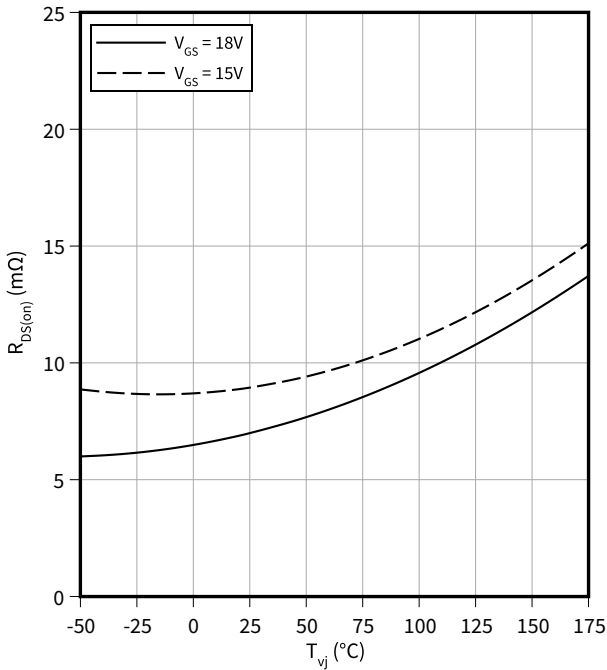
$I_{DS} = f(V_{DS})$
 $T_{vj} = 175\text{ °C}$, $t_p = 20\ \mu\text{s}$



4 Characteristics diagrams

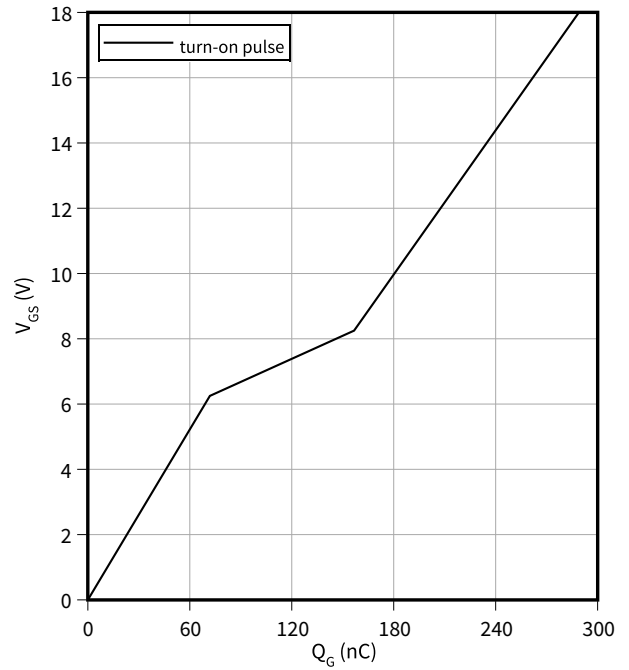
Typical on-state resistance as a function of junction temperature, MOSFET

$R_{DS(on)} = f(T_{vj})$
 $I_D = 108 \text{ A}$



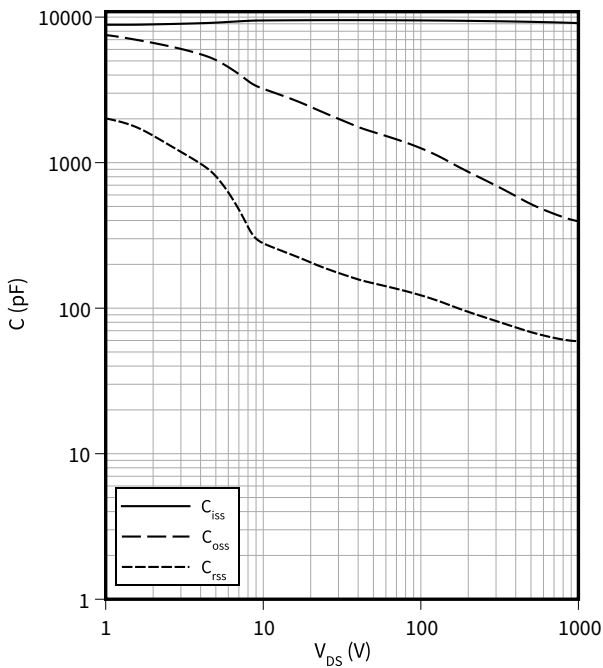
Typical gate charge, MOSFET

$V_{GS} = f(Q_G)$
 $I_D = 108 \text{ A}, V_{DS} = 800 \text{ V}$



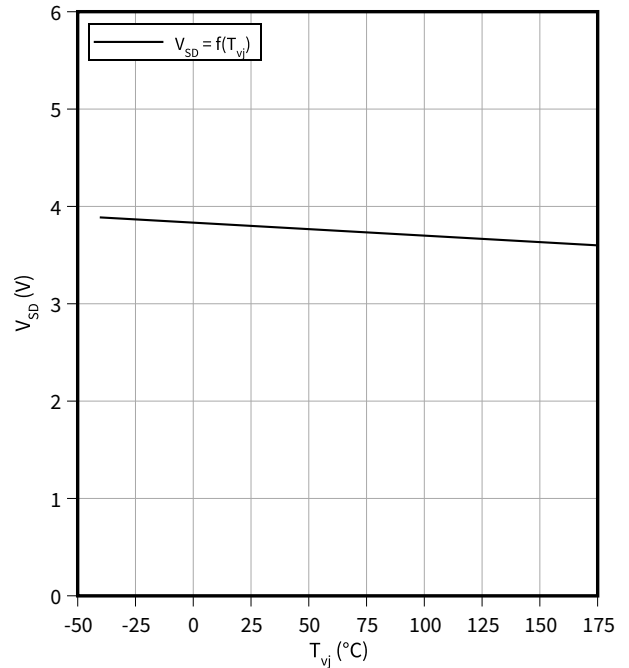
Typical capacitance as a function of drain-source voltage, MOSFET

$C = f(V_{DS})$
 $f = 100 \text{ kHz}, V_{GS} = 0 \text{ V}$



Typical reverse drain voltage as function of junction temperature, MOSFET

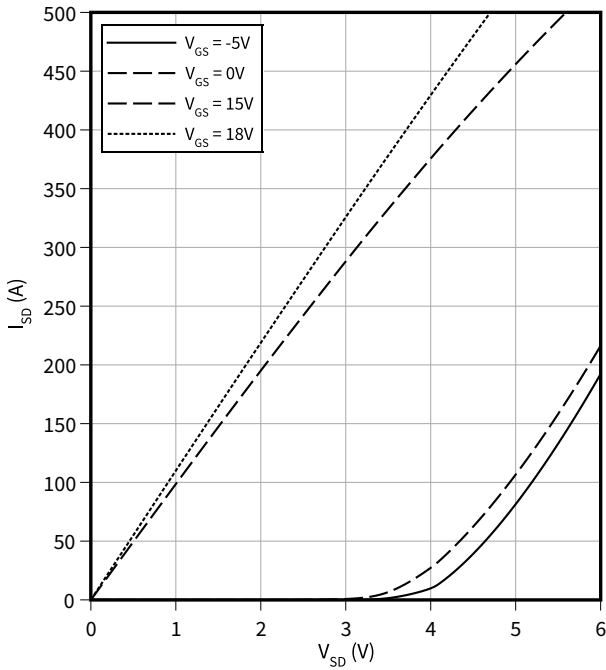
$V_{SD} = f(T_{vj})$
 $I_{SD} = 108 \text{ A}, V_{GS} = 0 \text{ V}$



4 Characteristics diagrams

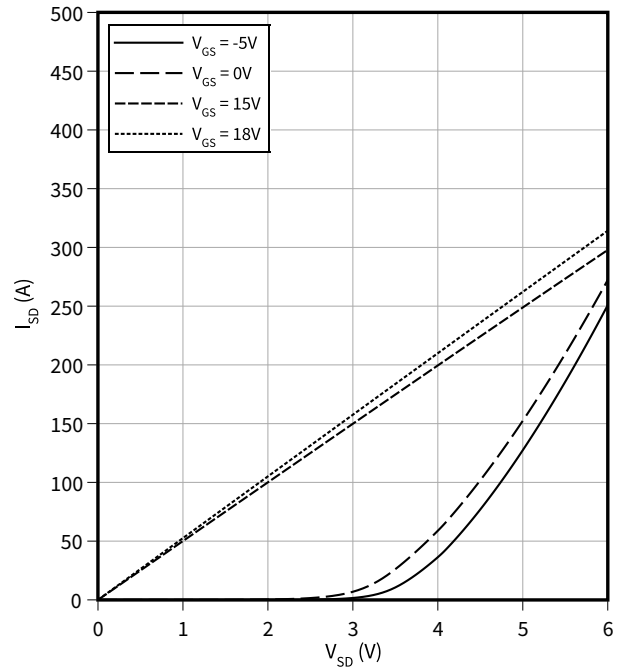
Typical reverse drain current as function of reverse drain voltage, V_{GS} as parameter, MOSFET

$I_{SD} = f(V_{SD})$
 $T_{vj} = 25\text{ °C}$, $t_p = 20\text{ }\mu\text{s}$



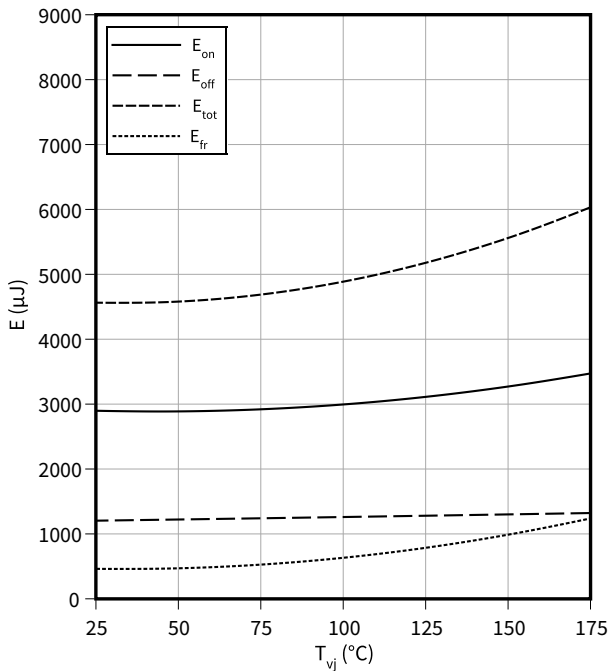
Typical reverse drain current as function of reverse drain voltage, V_{GS} as parameter, MOSFET

$I_{SD} = f(V_{SD})$
 $T_{vj} = 175\text{ °C}$, $t_p = 20\text{ }\mu\text{s}$



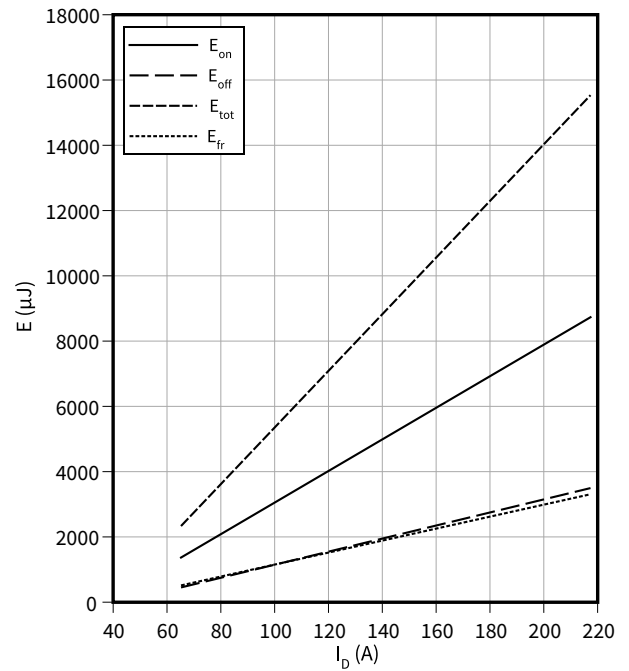
Typical switching energy as a function of junction temperature, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0\text{ V}$, MOSFET

$E = f(T_{vj})$
 $V_{GS} = 0/18\text{ V}$, $I_D = 108\text{ A}$, $R_{G,ext} = 1\text{ }\Omega$, $V_{DD} = 800\text{ V}$



Typical switching energy as a function of drain current, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0\text{ V}$, MOSFET

$E = f(I_D)$
 $T_{vj} = 175\text{ °C}$, $R_{G,ext} = 1\text{ }\Omega$, $V_{DD} = 800\text{ V}$, $V_{GS} = 0/18\text{ V}$

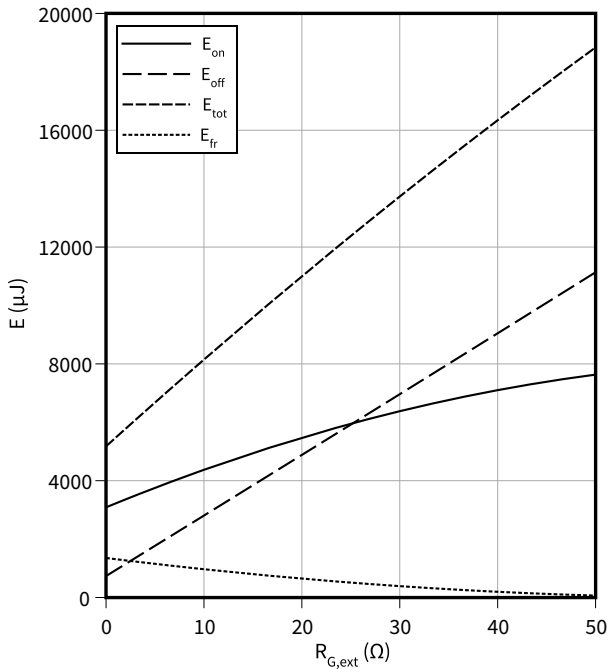


4 Characteristics diagrams

Typical switching energy losses as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V, MOSFET

$E = f(R_{G,ext})$

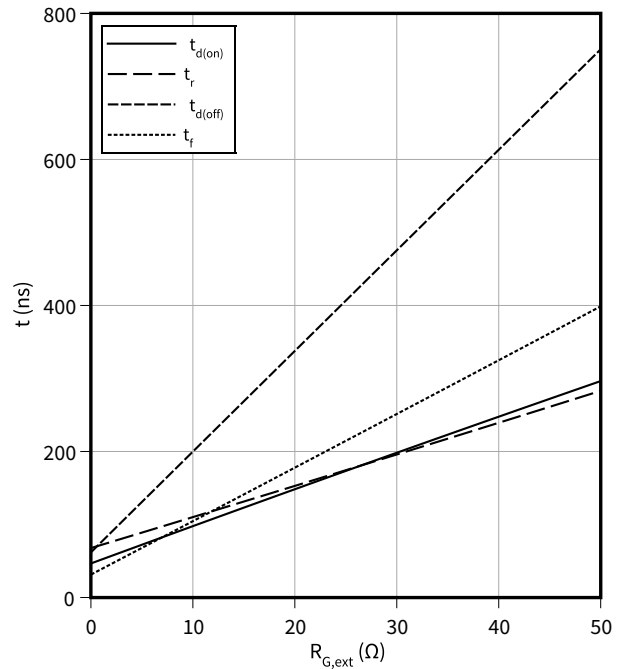
$V_{GS} = 0/18$ V, $I_D = 108$ A, $T_{vj} = 175$ °C, $V_{DD} = 800$ V



Typical switching times as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V, MOSFET

$t = f(R_{G,ext})$

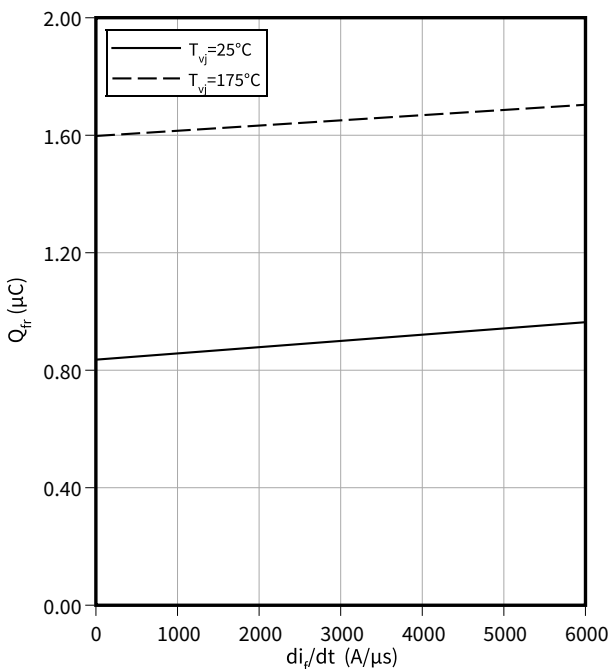
$V_{GS} = 0/18$ V, $I_D = 108$ A, $T_{vj} = 175$ °C, $V_{DD} = 800$ V



Typical reverse recovery charge as a function of reverse drain current slope, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V, MOSFET

$Q_{fr} = f(di_f/dt)$

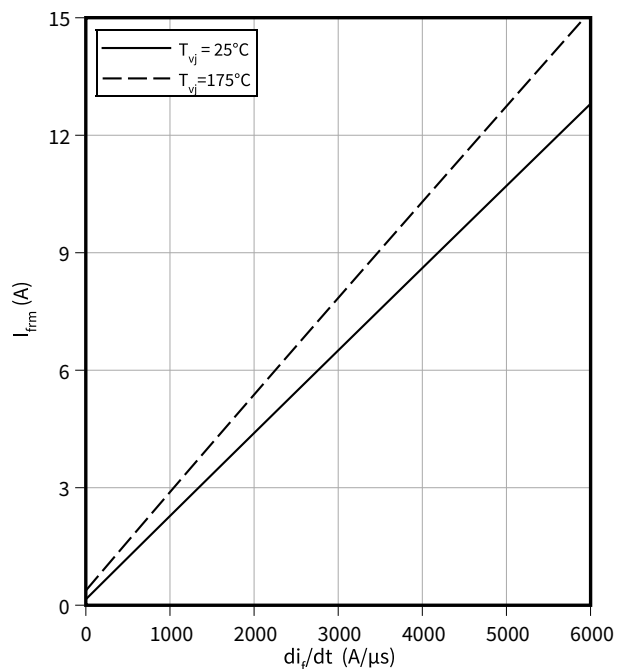
$V_{GS} = 0/18$ V, $I_D = 108$ A, $V_{DD} = 800$ V



Typical reverse recovery current as a function of reverse drain current slope, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V, MOSFET

$I_{frm} = f(di_f/dt)$

$V_{GS} = 0/18$ V, $I_D = 108$ A, $V_{DD} = 800$ V

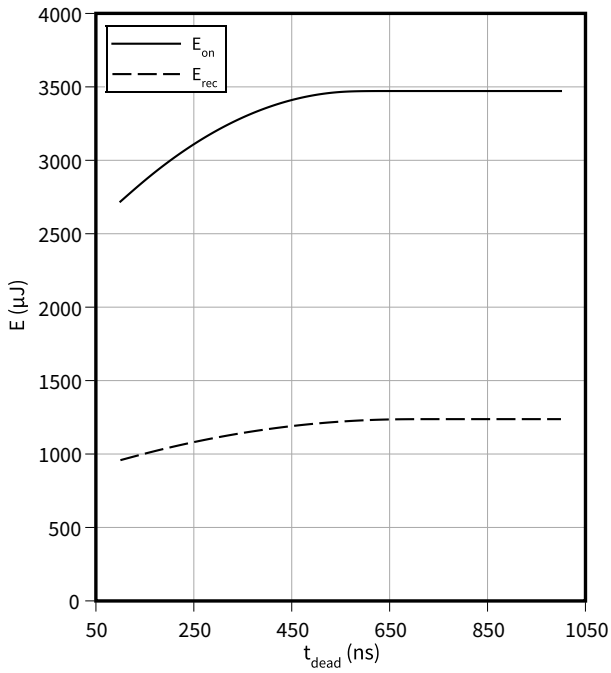


4 Characteristics diagrams

Typical switching energy losses as a function of dead time / blanking time, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = -5$ V, MOSFET

$$E = f(t_{dead})$$

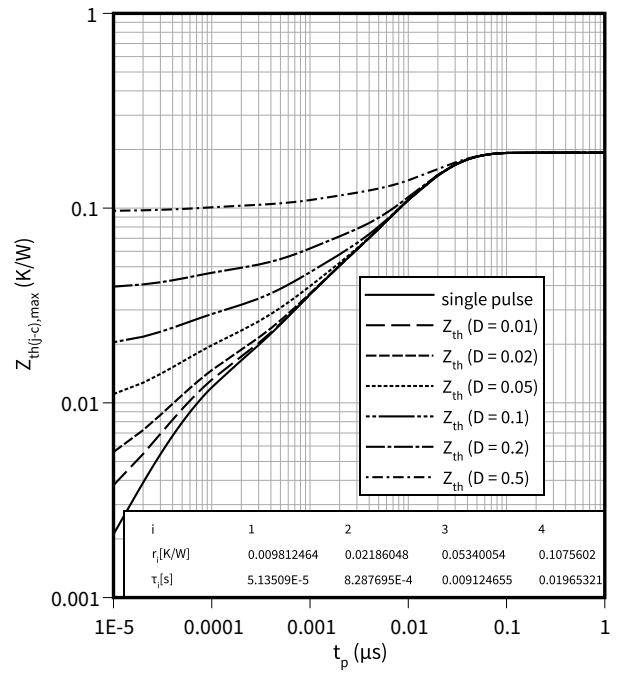
$V_{GS} = -5/18$ V, $I_D = 108$ A, $T_{vj} = 175$ °C, $V_{DD} = 800$ V



Max. transient thermal impedance (MOSFET/diode), MOSFET

$$Z_{th(j-c),max} = f(t_p)$$

$$D = t_p/T$$



5 Package outlines

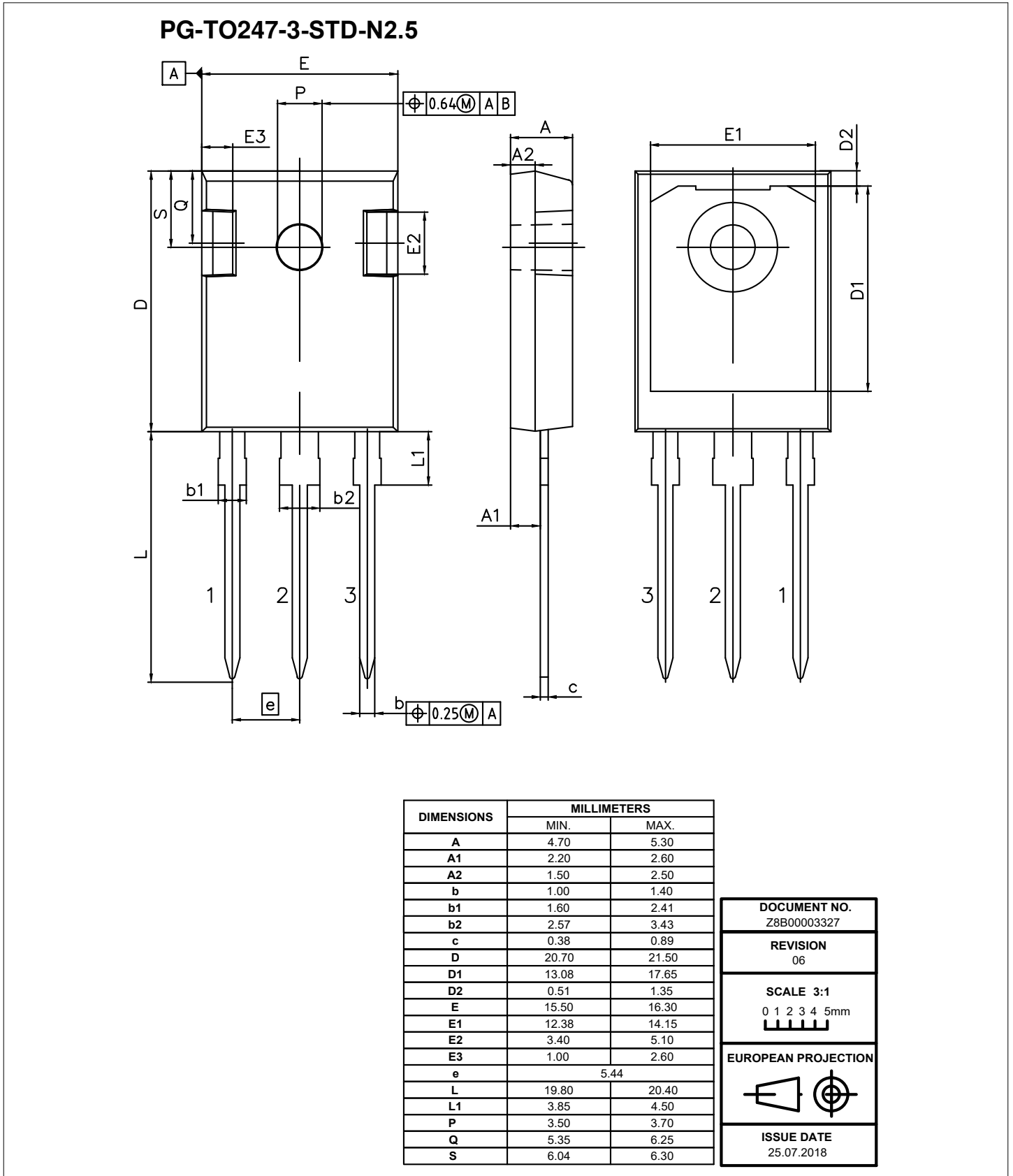


Figure 1

6 Testing conditions

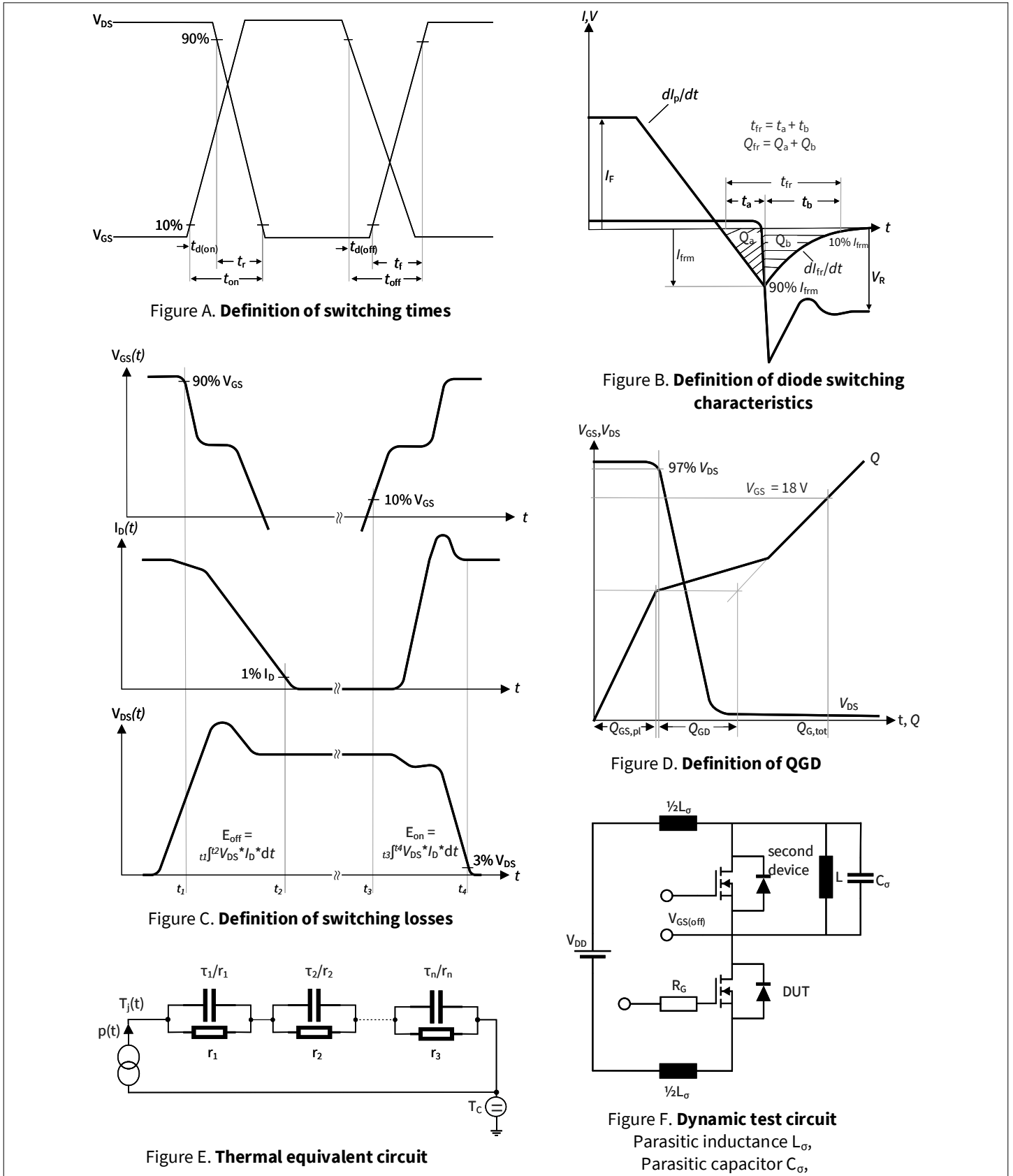


Figure 2

Revision history

Revision history

Document revision	Date of release	Description of changes
1.00	2022-01-31	Final datasheet

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